

NPN General Purpose Transistor

NST3904F3T5G

The NST3904F3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 100-300
- Low $V_{CE(sat)}$, $\leq 0.4 \text{ V}$
- Reduces Board Space
- This is a Pb-Free Device

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--------------------------------|------------------|-------|------|
| Collector - Emitter Voltage | V_{CEO} | 40 | Vdc |
| Collector - Base Voltage | V_{CBO} | 60 | Vdc |
| Emitter – Base Voltage | V _{EBO} | 6.0 | Vdc |
| Collector Current - Continuous | I _C | 200 | mAdc |

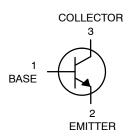
THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------------------------|----------------|-------------|
| Total Device Dissipation, T _A = 25°C Derate above 25°C | P _D (Note 1) | 290 2.3 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | R _{θJA} (Note 1) | 432 | °C/W |
| Total Device Dissipation, T _A = 25°C Derate above 25°C | P _D (Note 2) | 347 2.8 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | R _{θJA} (Note 2) | 360 | °C/W |
| Thermal Resistance, Junction-to-Lead 3 | R _{ΨJL} (Note 2) | 143 | °C/W |
| Junction and Storage Temperature Range | T _J , T _{stg} | -55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

- 1. 100 mm² 1 oz, copper traces.
 2. 500 mm² 1 oz, copper traces.





SOT-1123 **CASE 524AA** STYLE 1

MARKING DIAGRAM



= Device Code = Date Code

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------------|-----------------------|-----------------------|
| NST3904F3T5G | SOT-1123 (Pb-Free) | 8000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST3904F3T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| С | Symbol | Min | Max | Unit | |
|--|---|----------------------|-----------------------------|--------------------|-----|
| OFF CHARACTERISTICS | | • | · | • | |
| Collector - Emitter Breakdown Volta | V _{(BR)CEO} | 40 | - | Vdc | |
| Collector - Base Breakdown Voltage | V _{(BR)CBO} | 60 | - | Vdc | |
| Emitter - Base Breakdown Voltage (| V _{(BR)EBO} | 6.0 | - | Vdc | |
| Collector Cutoff Current (V _{CE} = 30 V | I _{CEX} | - | 50 | nAdc | |
| ON CHARACTERISTICS (Note 3) | | | | • | I |
| DC Current Gain | | h _{FE} | 40 70 100 60 30 | - 300 - - | - |
| Collector – Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc) | | V _{CE(sat)} | - - | 0.2 0.3 | Vdc |
| Base – Emitter Saturation Voltage ($I_C = 10$ mAdc, $I_B = 1.0$ mAdc) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) | | V _{BE(sat)} | 0.65 - | 0.85 1.0 | Vdc |
| SMALL-SIGNAL CHARACTERIST | TICS | | • | • | • |
| Current - Gain - Bandwidth Product | t (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz) | f _T | 200 | _ | MHz |
| Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz) | | C _{obo} | - | 4.0 | pF |
| Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz) | | C _{ibo} | - | 8.0 | pF |
| Noise Figure (V_{CE} = 5.0 Vdc, I_{C} = 100 μ Adc, R_{S} = 1.0 k Ω , f = 1.0 kHz) | | NF | - | 5.0 | dB |
| SWITCHING CHARACTERISTICS | | | | | • |
| Delay Time (| (V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc) | t _d | - | 35 | |
| Rise Time (| (I _C = 10 mAdc, I _{B1} = 1.0 mAdc) | t _r | - | 35 | ns |
| Storage Time (| (V _{CC} = 3.0 Vdc, I _C = 10 mAdc) | t _s | - | 275 | |
| Fall Time (| (I _{B1} = I _{B2} = 1.0 mAdc) | t _f | - | 50 | ns |

^{3.} Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

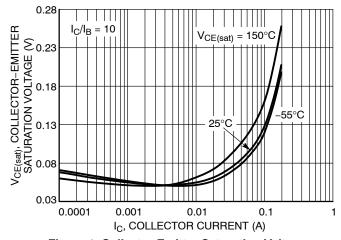


Figure 1. Collector Emitter Saturation Voltage vs.
Collector Current

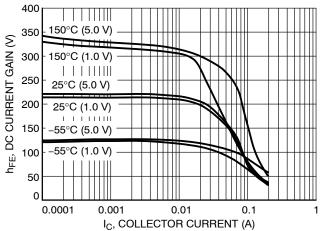


Figure 2. DC Current Gain vs. Collector Current

NST3904F3T5G

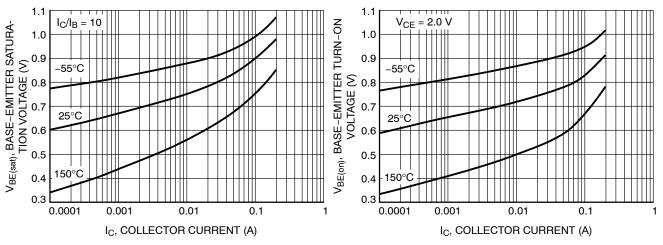


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

Figure 4. Base Emitter Turn-On Voltage vs. Collector Current

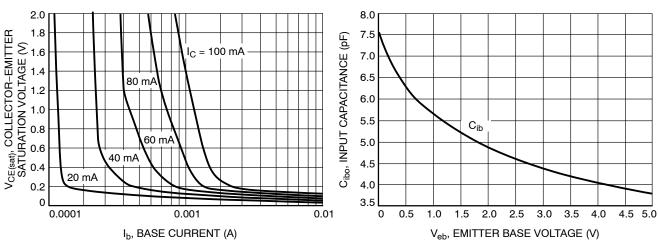


Figure 5. Saturation Region

Figure 6. Input Capacitance

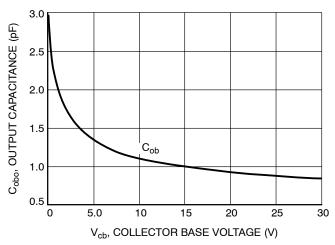


Figure 7. Output Capacitance



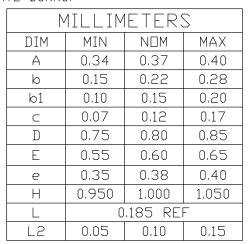


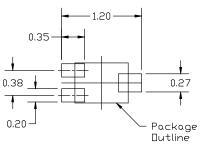
SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

DATE 18 JAN 2024

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
 DF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

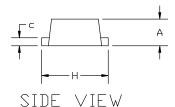


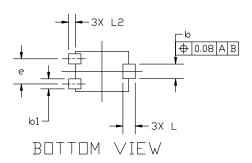


RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□L□ERRM/□.

| D | B |
|----------|---|
| | E |
| TOP VIEW | |





GENERIC MARKING DIAGRAM*



X = Specific Device Code

M = Date Code

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| STYLE 1: | STYLE 2: | STYLE 3: | STYLE 4: | STYLE 5: |
|-----------------------------|--------------|---------------------------|----------------|-------------|
| PIN 1. BASE | PIN 1. ANODE | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. GATE |
| 2. EMITTER | 2. N/C | 2. ANODE | 2. CATHODE | 2. SOURCE |
| COLLECTOR | 3. CATHODE | CATHODE | 3. ANODE | 3. DRAIN |

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|------------------|--------------------------------|---|-------------|--|
| DESCRIPTION: | SOT-1123 0.80x0.60x0.37, 0.35P | | PAGE 1 OF 1 | |

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